

| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|---|---------------------------|------------------|
| - | 0 | (""densified dielectric"").PN. | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 16:18 |
| - | 0 | (""densified"").PN. | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 17:15 |
| - | 0 | ("densified").PN. | USPAT | 2002/07/18 17:15 |
| - | 8939 | densification | USPAT | 2002/07/18 17:15 |
| - | 71 | densification near dielectric | USPAT | 2002/07/18 17:16 |
| - | 616 | densification same dielectric | USPAT | 2002/07/18 17:15 |
| - | 25 | (densification near dielectric) and plasma | USPAT | 2002/07/18 17:22 |
| - | 697 | "low k dielectric" | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 17:23 |
| - | 105 | "low k dielectric" same "etch stop" | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 17:38 |
| - | 1 | 6054379.pn. | USPAT | 2002/07/18 17:48 |
| - | 271 | treat\$3 near dielectric | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 17:49 |
| - | 87 | (treat\$3 near dielectric) and plasma | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 17:53 |
| - | 11 | ((treat\$3 near dielectric) and plasma) and "etch stop" | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 17:56 |
| - | 2 | 5314845.pn. | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 17:58 |
| - | 2 | 5915203.pn. | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 18:00 |
| - | 2 | ("6303047" "6365528").pn. | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 18:06 |
| - | 44591 | silicon with carbide | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 18:06 |
| - | 42528 | silicon with carbon | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 18:07 |
| - | 73891 | (silicon with carbide) or (silicon with carbon) | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 18:07 |
| - | 19286 | ((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen) | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 18:09 |
| - | 189 | (((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen)) and "low k" | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 18:10 |
| - | 167 | (((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen)) and "low k") and etch\$3 | USPAT; US-PGPUB; EPO; JPO | 2002/07/18 18:10 |
| - | 1620 | "dual damascene" and etch\$3 | USPAT; US-PGPUB; EPO; JPO | 2002/07/19 09:40 |
| - | 110 | ("dual damascene" and etch\$3) and "etch mask" | USPAT; US-PGPUB; EPO; JPO | 2002/07/19 09:40 |

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|---|-------|---|---------------------------|------------------|
| - | 103 | ((("dual damascene" and etch\$3) and "etch mask") and (vias via trenches trench)) | USPAT; US-PGPUB; EPO; JPO | 2002/07/19 09:42 |
| - | 101 | ((("dual damascene" and etch\$3) and "etch mask") and (vias via trenches trench)) and pattern\$3 | USPAT; US-PGPUB; EPO; JPO | 2002/07/19 09:42 |
| - | 39 | ((("dual damascene" and etch\$3) and "etch mask") and (vias via trenches trench)) and pattern\$3) and "low k" convert\$3 near6 dielectric | USPAT; US-PGPUB; EPO; JPO | 2002/07/19 09:49 |
| - | 1511 | (convert\$3 near6 dielectric) and etch\$ | USPAT; US-PGPUB; EPO; JPO | 2002/07/19 09:54 |
| - | 452 | (convert\$3 near6 dielectric) and etch\$ | USPAT; US-PGPUB; EPO; JPO | 2002/07/19 09:55 |
| - | 59 | ((convert\$3 near6 dielectric) and etch\$) and ("etch mask" "etch stop") | USPAT; US-PGPUB; EPO; JPO | 2002/07/19 09:55 |
| - | 226 | photoresist adj mask adj5 dielectric | USPAT; EPO; JPO | 2003/05/14 21:25 |
| - | 0 | (photoresist adj mask adj5 dielectric) and "densified dielectric" | USPAT; EPO; JPO | 2003/05/14 21:24 |
| - | 221 | (photoresist adj mask adj5 dielectric) and etch\$3 | USPAT; EPO; JPO | 2003/05/14 21:25 |
| - | 3240 | etch\$3 adj3 sidewall | USPAT; EPO; JPO | 2003/05/14 21:25 |
| - | 10 | (photoresist adj mask adj5 dielectric) and (etch\$3 adj3 sidewall) | USPAT; EPO; JPO | 2003/05/14 21:30 |
| - | 2493 | "low-k" "low k" | USPAT; EPO; JPO | 2003/10/09 13:48 |
| - | 1450 | ("low-k" "low k") with dielectric | USPAT; EPO; JPO | 2003/10/09 13:49 |
| - | 712 | (("low-k" "low k") with dielectric) and damascene | USPAT; EPO; JPO | 2003/10/09 13:49 |
| - | 532 | ((("low-k" "low k") with dielectric) and damascene) and plasma | USPAT; EPO; JPO | 2003/10/09 13:49 |
| - | 528 | ((("low-k" "low k") with dielectric) and damascene) and plasma) and etch\$3 | USPAT; EPO; JPO | 2003/10/09 13:49 |
| - | 10632 | "etch stop" "etch mask" | USPAT; EPO; JPO | 2003/10/09 13:49 |
| - | 309 | ("etch stop" "etch mask") and (((("low-k" "low k") with dielectric) and damascene) and plasma) and etch\$3) | USPAT; EPO; JPO | 2003/10/09 14:03 |
| - | 1 | 6,028,015.pn. | USPAT; EPO; JPO | 2003/10/09 14:04 |
| - | 1 | 6,028,015.pn. and photoresist | USPAT; EPO; JPO | 2003/10/09 14:08 |
| - | 1 | 6,028,015.pn. and mask | USPAT; EPO; JPO | 2003/10/09 14:09 |
| - | 1 | 6,028,015.pn. and pattern\$3 | USPAT; EPO; JPO | 2003/10/09 14:09 |